

WHAT IS CLAIMED IS:

1. A method for forming a conductor on a dielectric, comprising:
 - a) depositing a conductive thickfilm on the dielectric;
 - b) subsintering the conductive thickfilm;
 - c) patterning the conductive thickfilm to define at least one
5 conductor;
 - d) etching the conductive thickfilm to expose the at least one conductor; and
 - e) firing the at least one conductor at a full sintering temperature.
2. The method of claim 1, wherein the conductive thickfilm comprises gold.
3. The method of claim 1, wherein the conductive thickfilm comprises DuPont QG150.
4. The method of claim 1, wherein the dielectric is a glass dielectric.
5. The method of claim 1, wherein the dielectric is formed from KQ CL-90-7858 dielectric.
6. The method of claim 1, wherein said subsintering comprises subsintering at a peak temperature of about 725°C for about ten minutes.

7. The method of claim 6, wherein the conductive thickfilm comprises gold and the dielectric comprises a KQ dielectric.
8. The method of claim 7, wherein the KQ dielectric is KQ CL-90-7858.
9. The method of claim 1, wherein said subsintering comprises subsintering at a peak temperature between 725°C and 850°C.
10. The method of claim 9, wherein the conductive thickfilm comprises gold and the dielectric comprises a KQ dielectric.
11. The method of claim 10, wherein the KQ dielectric is KQ CL-90-7858.
12. The method of claim 1, further comprising depositing the conductive thickfilm on a substrate at about the same time the conductive thickfilm is deposited on the glass dielectric.
13. The method of claim 12, wherein the substrate is an alumina ceramic substrate.
14. The method of claim 12, wherein the subsintering is undertaken at a peak temperature that equalizes the etch rates of the conductive thickfilm on the substrate and the glass dielectric.

15. The method of claim 14, wherein the glass dielectric is formed from KQ CL-90-7858 dielectric.
16. The method of claim 14, wherein said subsintering comprises subsintering at a peak temperature of about 725°C for about ten minutes.
17. The method of claim 16, wherein the conductive thickfilm comprises gold and the dielectric comprises a KQ dielectric.
18. The method of claim 17, wherein the substrate is an alumina ceramic substrate.
19. The method of claim 14, wherein said subsintering comprises subsintering at a peak temperature between 700°C and 850°C.
20. The method of claim 1, further comprising, after firing, dipping the at least one conductor in an unheated solution of 10:1 hydrofluoric acid to de-ionized water for about ten seconds, and then rinsing the at least one conductor in de-ionized water.